

## Description

The AOD4184A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **General Features**

V<sub>DS</sub> = 40V I<sub>D</sub> =60A

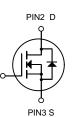
 $R_{DS(ON)} < 8.5 m\Omega$  @ V<sub>GS</sub>=10V

## Application

Battery protection

Load switch Uninterruptible power supply





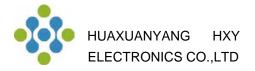
N-Channel MOSFET

#### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AOD4184A	TO-252-2L	HXY MOSFET	2500

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units	
Vds	Drain-Source Voltage	40	V	
Vgs	Gate-Source Voltage	±20	V	
I₀@Tc=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	nuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 60		
ID@Tc=100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	45	А	
Ідм	Pulsed Drain Current <sup>2</sup>	220	А	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	416.1	mJ	
las	Avalanche Current	39	A	
PD@Tc=25°C	Total Power Dissipation <sup>4</sup>	64.6	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Reja	Thermal Resistance Junction-ambient (Steady 62 State) <sup>1</sup>		°C/W	
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	2.8		

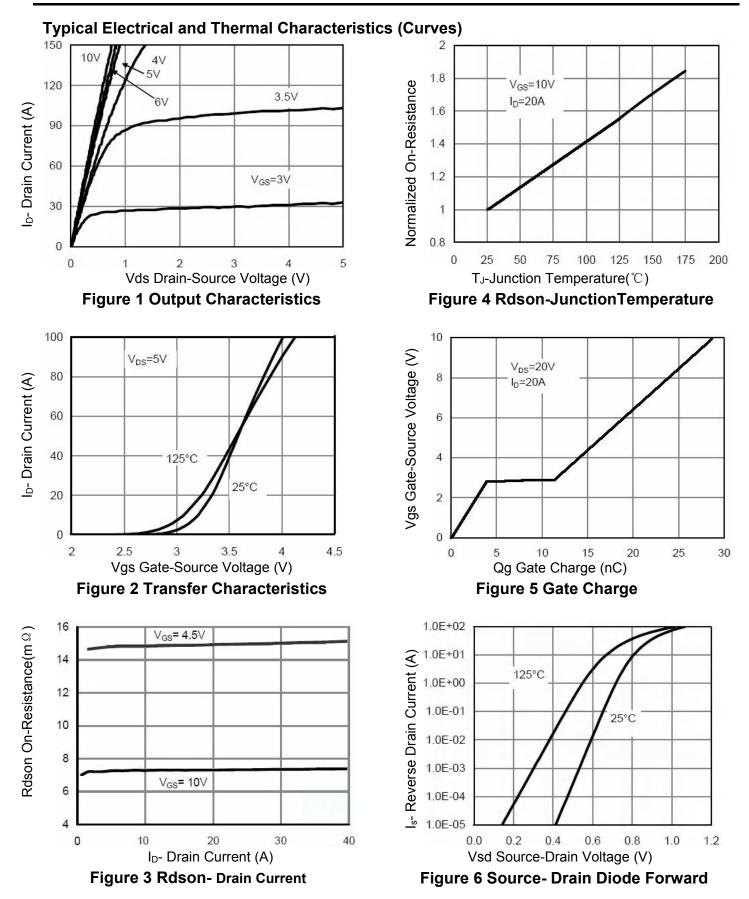


Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40	45	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)	·						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.2	1.6	2.0	V	
	Р	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	7.0	8.5	mΩ	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		15	18		
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	15	-	-	S	
Dynamic Characteristics (Note4)	·						
Input Capacitance	C <sub>lss</sub>		-	1800	-	PF	
Output Capacitance	Coss	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V, F=1.0MHz	-	280	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	190	-	PF	
Switching Characteristics (Note 4)	·		·				
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V,I <sub>D</sub> =2A,R <sub>L</sub> =1Ω	-	6.4	-	nS	
Turn-on Rise Time	tr		-	17.2	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>G</sub> =3Ω	-	29.6	-	nS	
Turn-Off Fall Time	tr		-	16.8	-	nS	
Total Gate Charge	Qg	V <sub>DS</sub> =20V,I <sub>D</sub> =20A,	-	29		nC	
Gate-Source Charge	Q <sub>gs</sub>		-	4.5		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	6.4		nC	
Drain-Source Diode Characteristics	·		•				
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	68	A	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	29	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	26	-	nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				y LS+LD	

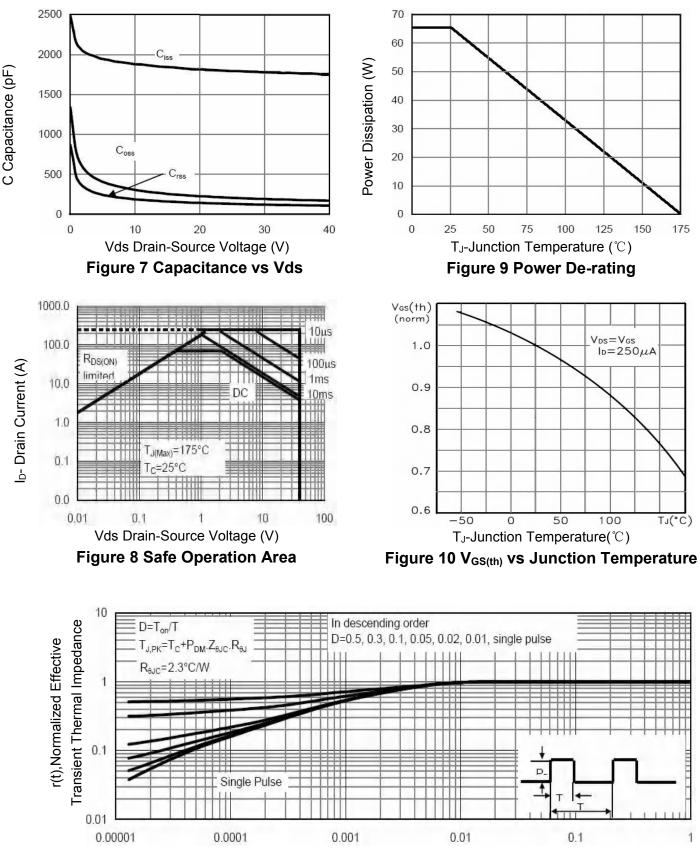
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.**  $E_{AS}$  condition : Tj=25°C,  $V_{DD}$ =20V,  $V_{G}$ =10V,L=1mH, Rg=25 $\Omega$ ,

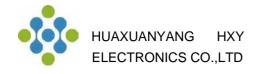




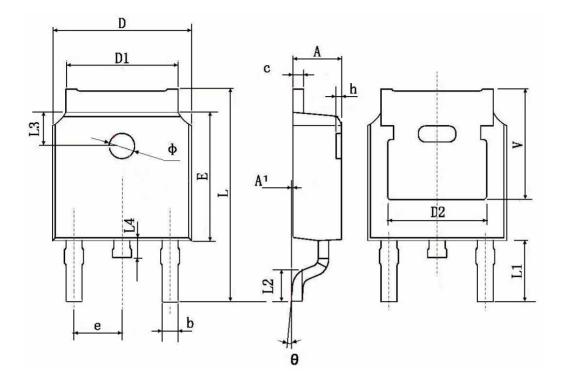




Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



# TO-252-2L Package Information



0hal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400 1.700		0.055	0.067	
L3	1.600	TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0 °	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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